

# Juan Colmenares

## List of Publications by Year in descending order

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18  
papers

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times ranked

527  
citing authors

#	ARTICLE	IF	CITATIONS
1	Comparison of Thermal Stress During Short-Circuit in Different Types of 1.2-kV SiC Transistors Based on Experiments and Simulations. IEEE Transactions on Industrial Electronics, 2021, 68, 2608-2616.	7.9	12
2	Design, Operation, and Loss Characterization of a 1-kW GaN-Based Three-Level Converter at Cryogenic Temperatures. IEEE Transactions on Power Electronics, 2020, 35, 12040-12052.	7.9	42
3	An IGBT Turn-ON Concept Offering Low Losses Under Motor Drive dv/dt Constraints Based on Diode Current Adaption. IEEE Transactions on Power Electronics, 2018, 33, 1143-1153.	7.9	23
4	Experimental evaluation of a 1 kW, single-phase, 3-level gallium nitride inverter in extreme cold environment. , 2017, , .		26
5	Introduction of SiC MOSFETs in converters based on Si IGBTs. , 2017, , .		7
6	Analysis of Parasitic Elements of SiC Power Modules With Special Emphasis on Reliability Issues. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2016, 4, 988-995.	5.4	46
7	Experimental characterization of enhancement mode gallium-nitride power field-effect transistors at cryogenic temperatures. , 2016, , .		27
8	Reliability Analysis of a High-Efficiency SiC Three-Phase Inverter. IEEE Journal of Emerging and Selected Topics in Power Electronics, 2016, 4, 996-1006.	5.4	16
9	Analysis of parasitic elements of SiC power modules with special emphasis on reliability issues. , 2016, , .		9
10	Short-Circuit Protection Circuits for Silicon-Carbide Power Transistors. IEEE Transactions on Industrial Electronics, 2016, 63, 1995-2004.	7.9	121
11	High-Efficiency 312-kVA Three-Phase Inverter Using Parallel Connection of Silicon Carbide MOSFET Power Modules. IEEE Transactions on Industry Applications, 2015, 51, 4664-4676.	4.9	51
12	An experimental analysis on how the dead-time of SiC BJT and SiC MOSFET impacts the losses in a high-frequency resonant converter. , 2014, , .		10
13	High-efficiency three-phase inverter with SiC MOSFET power modules for motor-drive applications. , 2014, , .		13
14	Switching performance of parallel-connected power modules with SiC MOSFETs. , 2014, , .		19
15	Dual-Function Gate Driver for a Power Module With SiC Junction Field-Effect Transistors. IEEE Transactions on Power Electronics, 2014, 29, 2367-2379.	7.9	17
16	Dual-function gate driver for a power module with SiC junction field transistors. , 2013, , .		2
17	Experimental investigations of static and transient current sharing of parallel-connected silicon carbide MOSFETs. , 2013, , .		63
18	Comparison of Thermal Stress during Short-Circuit in Different Types of 1.2 kV SiC Transistors Based on Experiments and Simulations. Materials Science Forum, 0, 897, 595-598.	0.3	2